

Prepared		Product Specifications AN17831A	Ref No.	A-1
Checked			Total Page	9
Approved			Page No.	1

Structure	Silicon Monolithic Bipolar IC
Appearance	SIL-12 Pins Plastic Package (FP-12S Power Type With Fin)
Application	Audio
Function	44W (6Ω) x 2ch BTL Power Amplifier Built-in Standby and Muting Features Incorporating Various Protection Circuits

A	Absolute Maximum Ratings				
No.	Item	Symbol	Ratings	Unit	Note
1	Storage Temperature	Tstg	-55 ~ +150	°C	
2	Operating Ambient Temperature	Topr	-25 ~ +75	°C	
3	Operating Ambient Pressure	Popr	1.013x10 ⁵ ± 0.01x10 ⁵	Pa	
4	Operating Constant Acceleration	Gopr	9,810	m/s ²	
5	Operating Shock	Sopr	4,900	m/s ²	
6	Power Supply Voltage	Vcc	27	V	1
7	Power Supply Current	Icc	8.0	A	
8	Power Dissipation	Pd	37.5	W	2

Operating Supply Voltage Range	Vcc	8.0 V ~ 24.0 V
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Note: 1) Without input signal, Vcc is up to 27V
2) Ta = 75°C with infinite heatsink

Eff. Date	Eff. Date	Eff. Date	Eff. Date	
18-FEB-2002				

Prepared		Product Specifications AN17831A	Ref No.	B-1
Checked			Total Page	9
Approved			Page No.	2

B Electrical Characteristics < Vcc = 12V, RL = 4Ω, freq. = 1 kHz, 2 Channel Outputs > (Unless otherwise specified, the ambient temperature is 25°C±2°C)									
No.	Item	Symbol	Test Cct.	Condition	Limit			Unit	Note
					Min	Typ	Max		
1	Quiescent Circuit Current	Ic _q	1	V _{in} =0mV	-	150	300	mA	
2	Output Noise Voltage	V _{no}	1	V _{in} =0mV, R _g =20kΩ	-	0.27	0.5	mV _{rms}	1
3	Voltage Gain	G _{vc}	1	V _{in} =20mV	38	40	42	dB	
4	Total Harmonic Distortion	THD	1	V _{in} =20mV	-	0.07	0.4	%	2
5	Maximum Output Power 1	P _{o1}	1	THD=10%	12	15	-	W	
6	Maximum Output Power 2	P _{o2}	1	V _{CC} =24V, R _L =6Ω, THD=10%	30	44	-	W	
7	Channel Balance	CB	1	V _{in} =20mV	-1	0	1	dB	
8	Channel Crosstalk	CT	1	V _{in} =20mV, R _g =20kΩ	55	70	-	dB	2
9	Output Offset Voltage	V _{off}	1	R _g =20kΩ	-350	0	350	mV	
10	Ripple Rejection	RR	1	V _r =1V _{rms} , f _r =120Hz, R _g =20kΩ	50	60	-	dB	1
11	Standby Current	I _{stb}	1	V _{in} =0mV	-	1	10	μA	
12	Muting Effects	MT	1	V _{in} =20mV	70	80	-	dB	2

Note : 1) With a filter band 20Hz ~20kHz (12 dB/OCT) used.

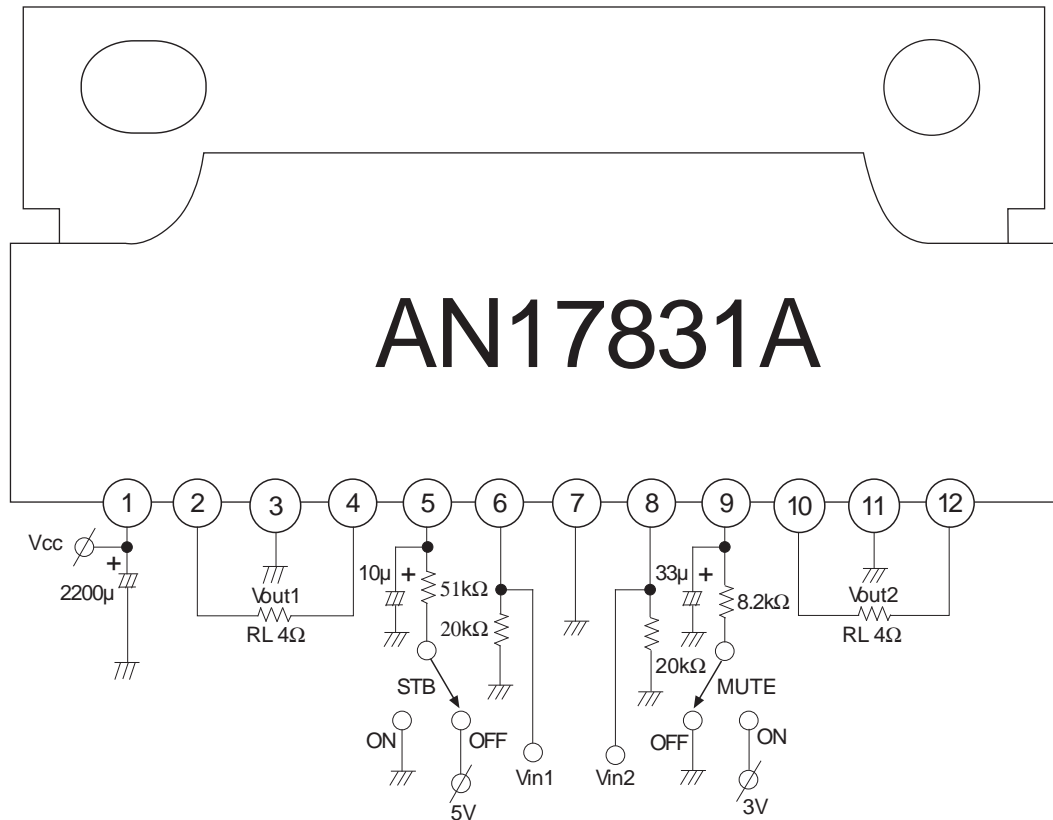
2) With a filter band 400Hz ~30kHz used.

Eff. Date	Eff. Date	Eff. Date	Eff. Date	
18-FEB-2002				www.DataSheet4U.com

Prepared		Product Specifications AN17831A	Ref No.	C-1
Checked			Total Page	9
Approved			Page No.	3

Description of Test Circuits and Test Methods

[Test Circuit 1]

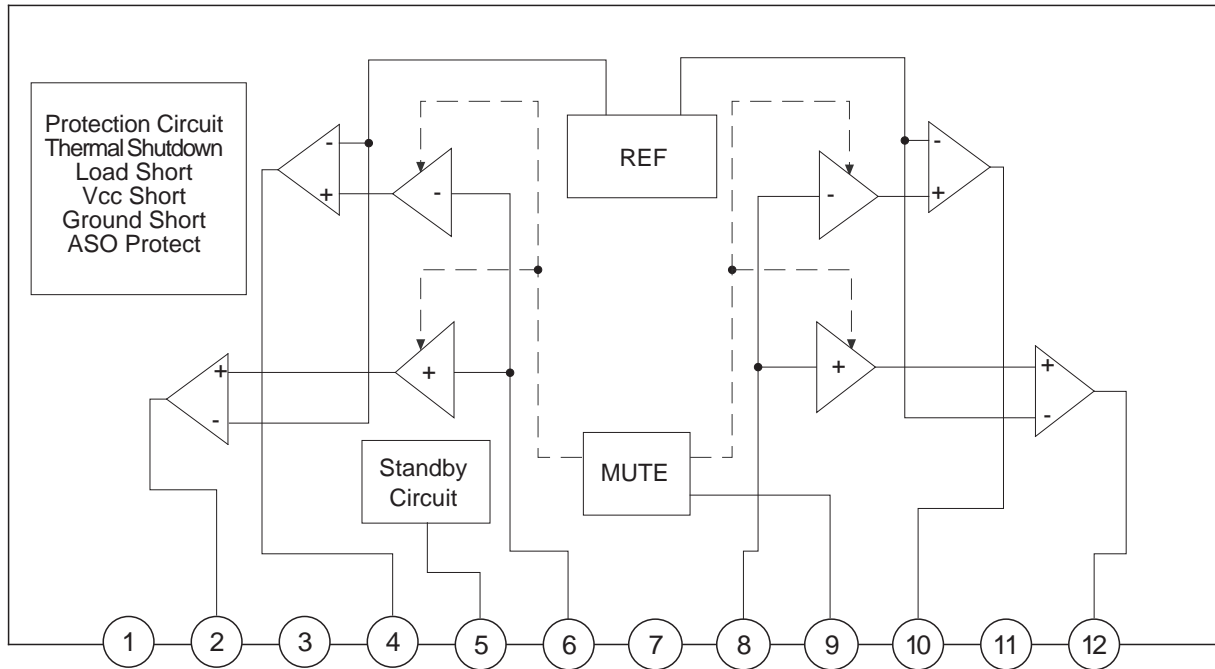


Note : * STB 'OFF' means 5V.
MUTE 'OFF' means 0V.

Eff. Date	Eff. Date	Eff. Date	Eff. Date	
18-FEB-2002				

Prepared		Product Specifications AN17831A	Ref No.	D-1
Checked			Total Page	9
Approved			Page No.	4

Circuit Function Block Diagram



Pin Descriptions

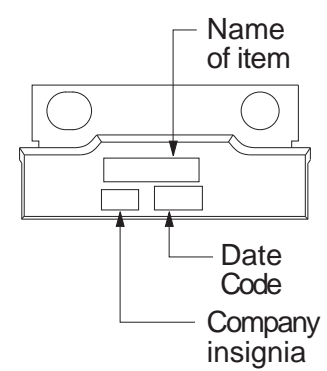
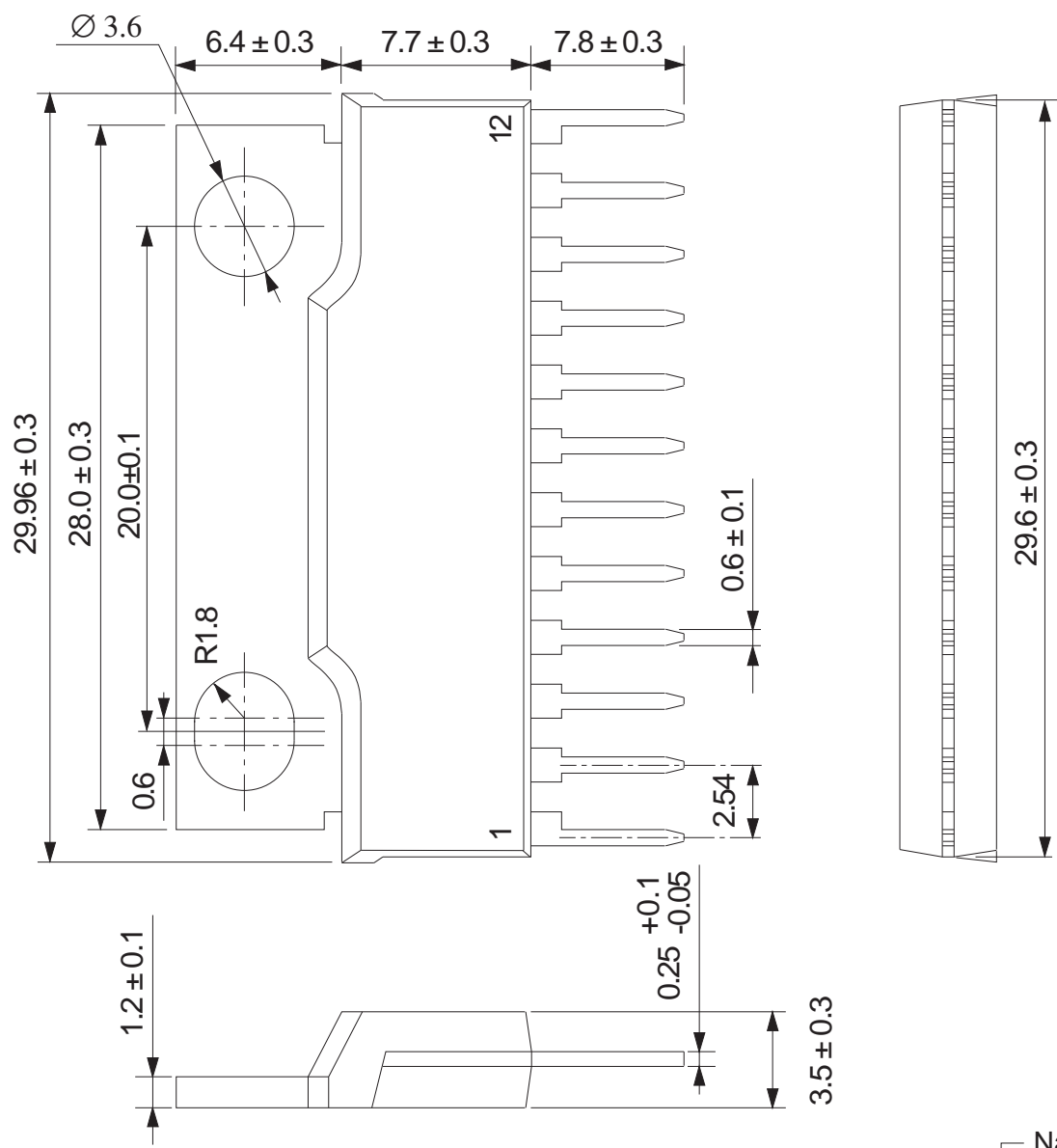
Pin No.	Pin Descriptions	Pin No.	Pin Descriptions
1	Vcc	7	Pre GND
2	Ch1 +ve Phase Output	8	Ch2 Input
3	Ch1 Output GND	9	Mute
4	Ch1 -ve Phase Output	10	Ch2 -ve Phase Output
5	Standby	11	Ch2 Output GND
6	Ch1 Input	12	Ch2 +ve Phase Output

Eff. Date	Eff. Date	Eff. Date	Eff. Date
18-FEB-2002			

Prepared		Product Specifications AN17831A	Ref No.	E
Checked			Total Page	9
Approved			Page No.	5

Package Name	FP-12S
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Unit : mm



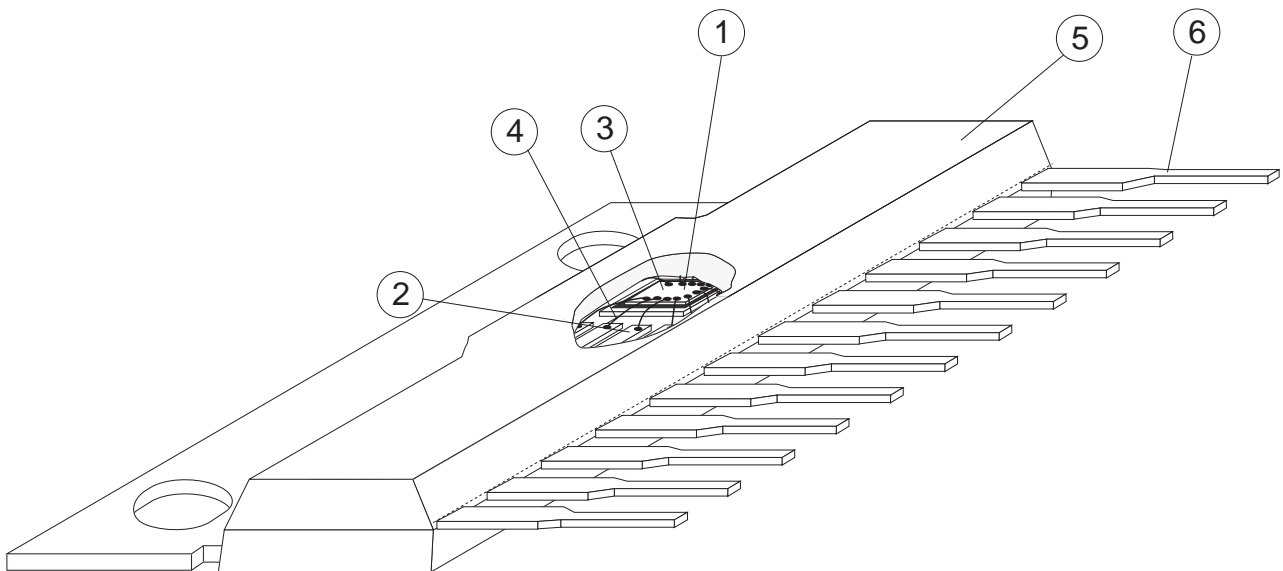
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18-FEB-2002			

Prepared		Product Specifications AN17831A	Ref No.	F-1
Checked			Total Page	9
Approved			Page No.	6

(Structure Description)

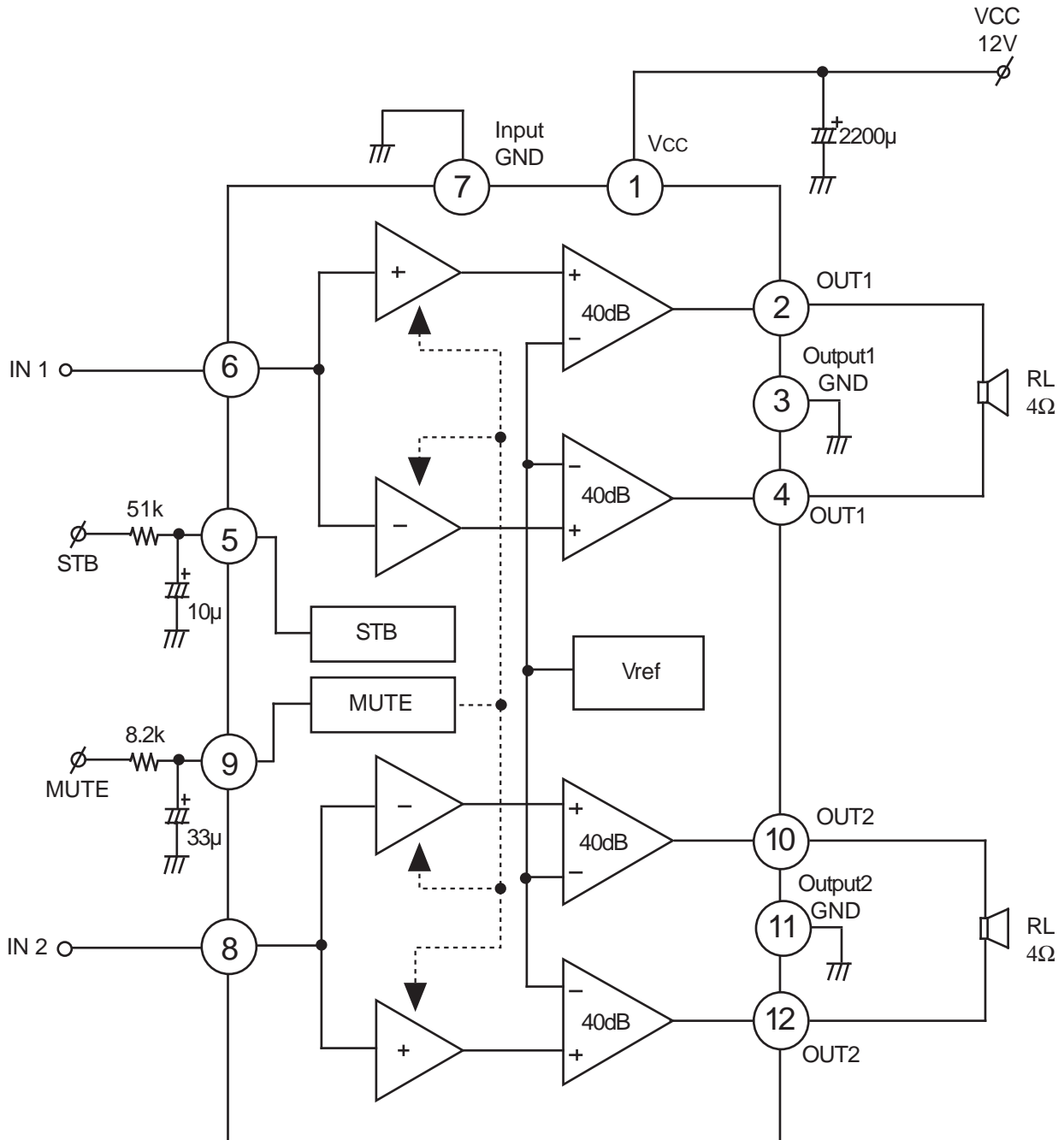
Chip surface passivation	SiN, PSG, Others ()	①
Lead frame material	Fe group, Cu group, Others ()	②, ⑥
Inner lead surface process	Ag plating, Au plating, Others ()	②
Outer lead surface process	Solder plating, Solder dip, Others ()	⑥
Chip mounting method	Ag paste, Au-Si alloy, Solder, Others ()	③
Wire bonding method	Thermalsonic bonding, Others ()	④
Mold material	Epoxy, Others ()	④
Molding method	Transfer mold, Multiplunger mold, Others ()	⑤
Fin material	Cu Group, Others ()	⑤

Package FP-12S



Eff. Date	Eff. Date	Eff. Date	Eff. Date
18-FEB-2002			

Application Circuit



STB 'OFF'	5V
STB 'ON'	0V
Mute 'OFF'	0V
Mute 'ON'	3V

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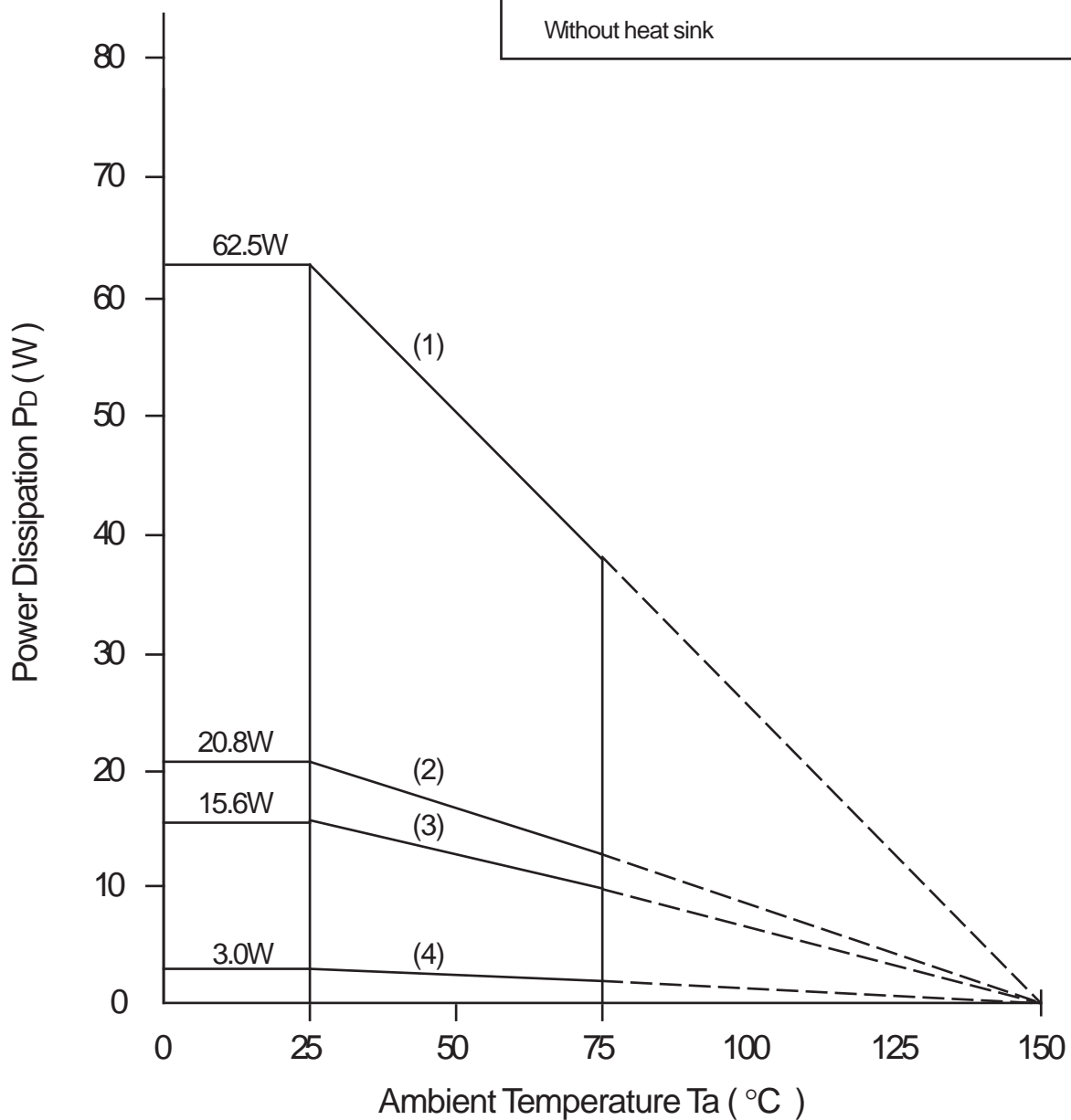
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18-FEB-2002

Prepared		Product Specifications AN17831A	Ref No.	G-2
Checked			Total Page	9
Approved			Page No.	8

PD - Ta Curves

- (1) $T_c = T_a$, 62.5W ($\theta_{j-c} = 2^\circ\text{C/W}$)
- (2) 20.83W ($\theta_f = 4.0^\circ\text{C/W}$)
With a 100cm²X 3mmAl heat sink (black colour coated)
or a 200cm²X 2mmAl heat sink (not lacquered)
- (3) 15.63W ($\theta_f = 6.0^\circ\text{C/W}$)
With a 100cm²X 2mmAl heat sink (not lacquered)
- (4) 3.0W at $T_a = 25^\circ\text{C}$ ($\theta_{j-a} = 42^\circ\text{C/W}$)
Without heat sink



Eff. Date	Eff. Date	Eff. Date	Eff. Date	
18-FEB-2002				

Prepared		Product Specifications AN17831A	Ref No.	H-1
Checked			Total Page	9
Approved			Page No.	9

(Precautions for use)

- 1) Be sure to attach a heat sink to the IC before use. Make sure that the heat sink is secured to the chassis.
- 2) Ground the radiation fin so that there will be no difference in electric potential between the radiation fin and ground.
- 3) The thermal protection circuit operates at a T_j of approximately 150°C. The thermal protection circuit is reset automatically when the temperature drops.
- 4) The overvoltage protection circuit operates at a V_{cc} of approximately 28V.
- 5) Use a stabilised power supply with a 3V or higher standby voltage.

Eff. Date	Eff. Date	Eff. Date	Eff. Date	
18-FEB-2002				